



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- Complementary Pair: One 3904-Type NPN
One 3906-Type PNP
- Ultra-Small Surface Mount Package
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

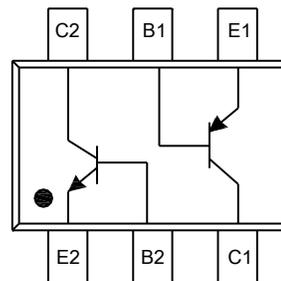
Mechanical Data

- Package: SOT363
- Package Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per
MIL-STD-202, Method 208 
- Weight: 0.006 grams (Approximate)

SOT363



Top View



E1, B1, C1 = PNP 3906
E2, B2, C2 = NPN 3904

Device Schematic and Pinout
Top View

Absolute Maximum Ratings, NPN 3904 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CE0}	40	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current	I _C	200	mA

Absolute Maximum Ratings, PNP 3906 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CE0}	-40	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-200	mA

Thermal Characteristics, Total Device (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Note: 5. For a device mounted on minimum recommended pad layout that is on a single-sided 0.6mm FR-4 PCB; device is measured under still air conditions while operating in a steady state.

Thermal Characteristics and Derating Information

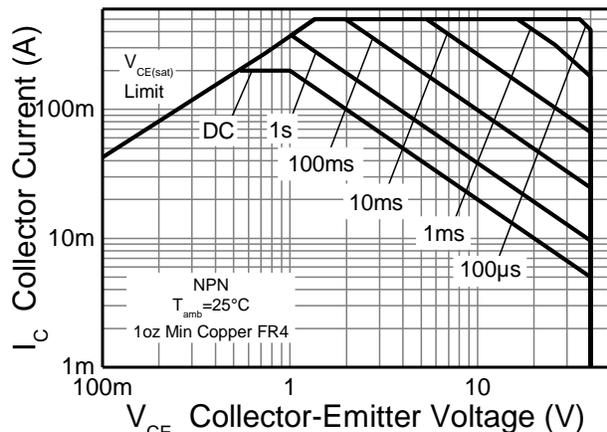


Fig. 1 NPN - Safe Operating Area

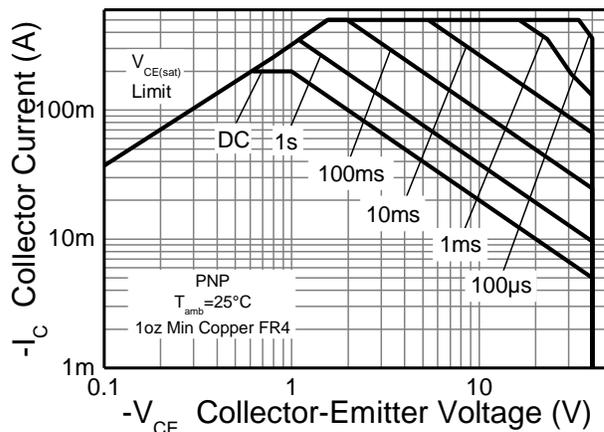


Fig. 2 PNP - Safe Operating Area

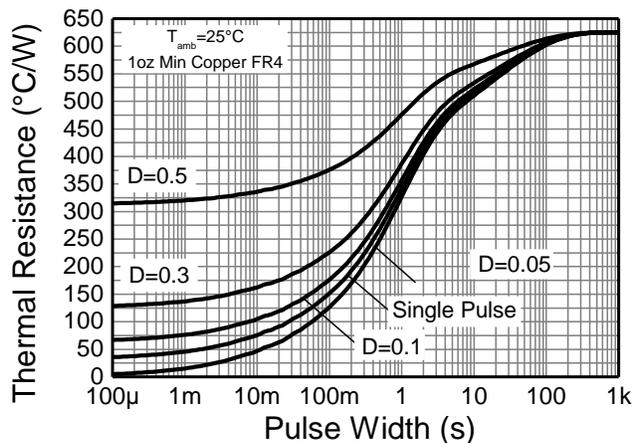


Fig. 3 Transient Thermal Impedance

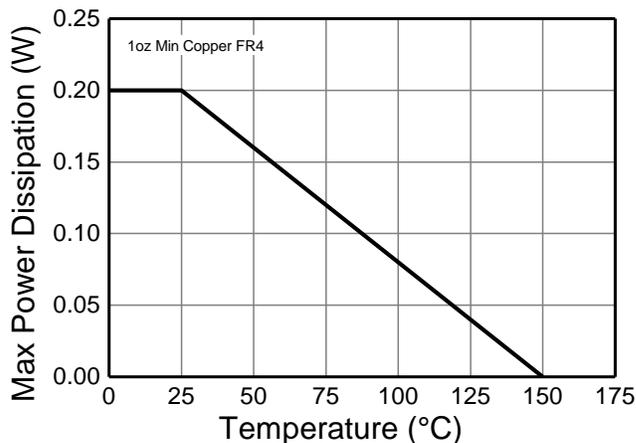


Fig. 4 Derating Curve

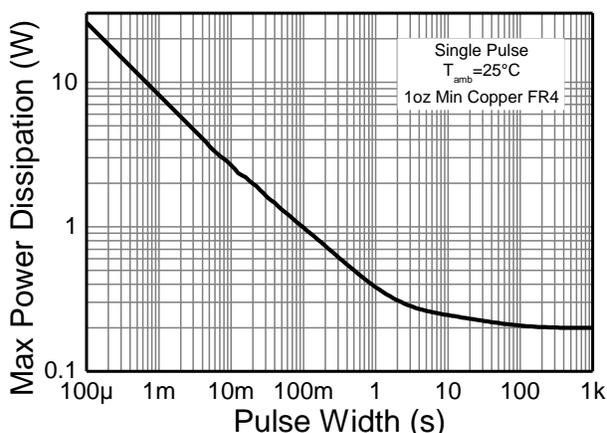


Fig. 5 Pulse Power Dissipation

Electrical Characteristics, NPN 3904 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	BV_{CBO}	60	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	40	—	V	$I_C = 1\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3\text{V}$
Base Cutoff Current	I_{BL}	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3\text{V}$
ON CHARACTERISTICS (Note 6)					
Static Forward Current Transfer Ratio	h_{FE}	40 70 100 60 30	— — 300 — —	—	$I_C = 100\mu\text{A}, V_{CE} = 1\text{V}$ $I_C = 1\text{mA}, V_{CE} = 1\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1\text{V}$ $I_C = 50\text{mA}, V_{CE} = 1\text{V}$ $I_C = 100\text{mA}, V_{CE} = 1\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	0.20 0.30	V	$I_C = 10\text{mA}, I_B = 1\text{mA}$ $I_C = 50\text{mA}, I_B = 5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	0.65 —	0.85 0.95	V	$I_C = 10\text{mA}, I_B = 1\text{mA}$ $I_C = 50\text{mA}, I_B = 5\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.0	pF	$V_{CB} = 5\text{V}, f = 1\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	—	8.0	pF	$V_{EB} = 0.5\text{V}, f = 1\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	1	10	k Ω	$V_{CE} = 10\text{V}, I_C = 1\text{mA}, f = 1\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.5	8	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	1	40	μS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	$V_{CE} = 20\text{V}, I_C = 20\text{mA}, f = 100\text{MHz}$
Noise Figure	NF	—	5	dB	$V_{CE} = 5\text{V}, I_C = 100\mu\text{A}, R_S = 1\text{k}\Omega, f = 1\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	$V_{CC} = 3\text{V}, I_C = 10\text{mA}$
Rise Time	t_r	—	35	ns	$V_{BE(off)} = 0.5\text{V}, I_{B1} = 1\text{mA}$
Storage Time	t_s	—	200	ns	$V_{CC} = 3\text{V}, I_C = 10\text{mA}$
Fall Time	t_f	—	50	ns	$I_{B1} = -I_{B2} = 1\text{mA}$

 Note: 6. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics, NPN 3904 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

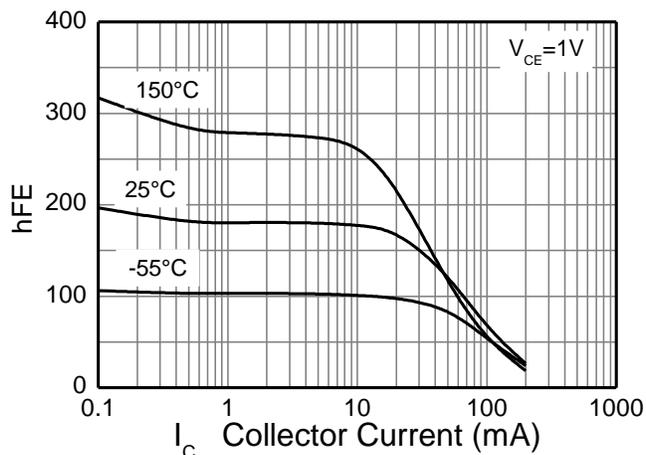


Fig. 6 $h_{FE} \ v \ I_C$

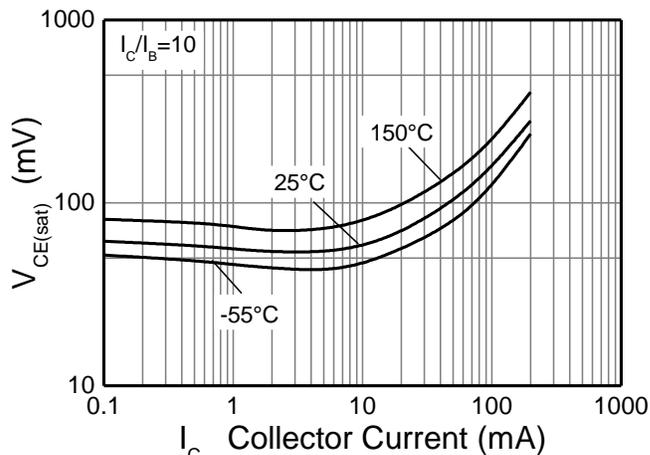


Fig. 7 $V_{CE(sat)} \ v \ I_C$

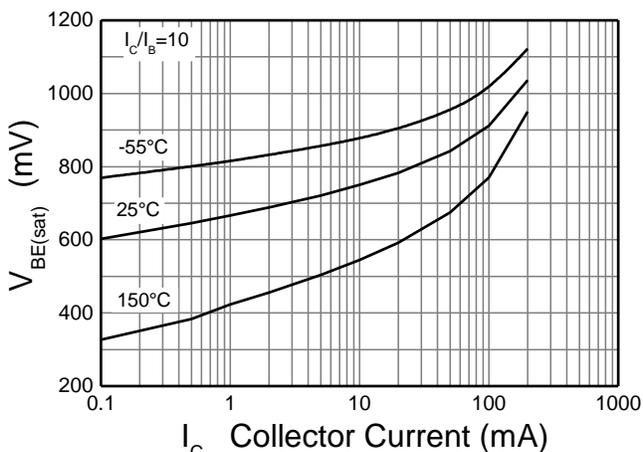


Fig. 8 $V_{BE(sat)} \ v \ I_C$

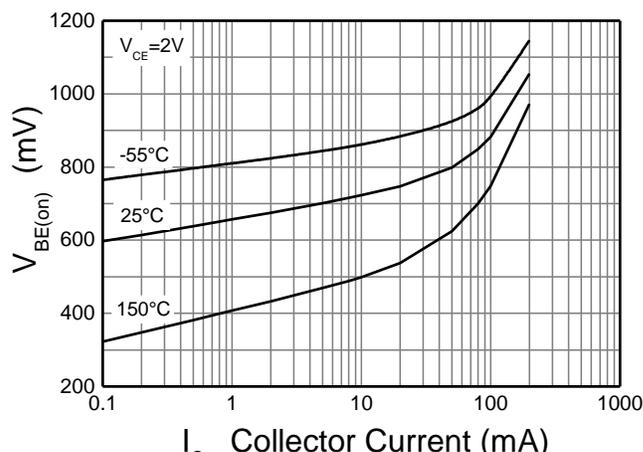


Fig. 9 $V_{BE(on)} \ v \ I_C$

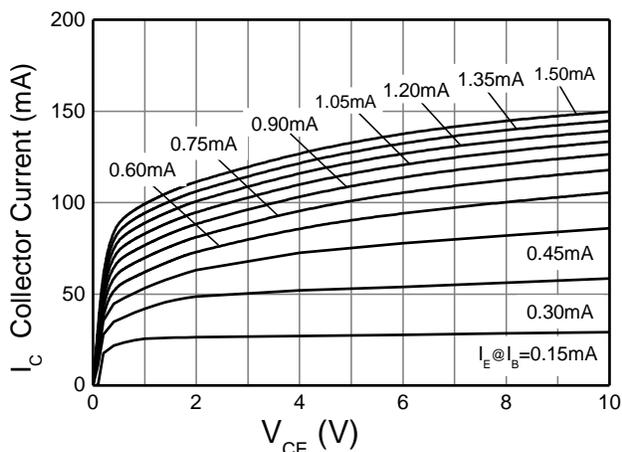


Fig. 10 $I_C \ v \ V_{CE}$

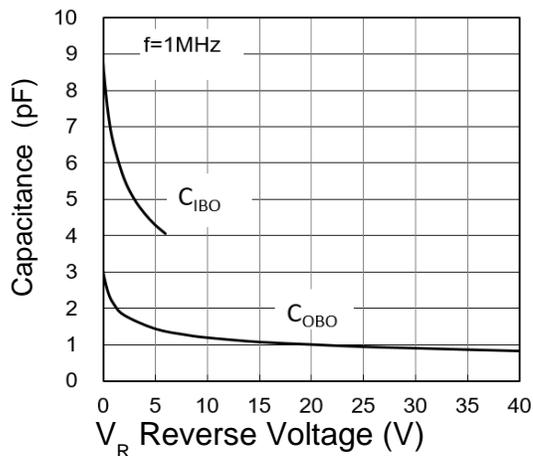


Fig. 11 Capacitance $v \ V_R$

Electrical Characteristics, PNP 3906 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40	—	V	$I_C = -1\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3\text{V}$
Base Cutoff Current	I_{BL}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3\text{V}$
ON CHARACTERISTICS (Note 6)					
Static Forward Current Transfer Ratio	h_{FE}	60 80 100 60 30	— — 300 — —	—	$I_C = -100\mu\text{A}, V_{CE} = -1\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -1\text{V}$ $I_C = -10\text{mA}, V_{CE} = -1\text{V}$ $I_C = -50\text{mA}, V_{CE} = -1\text{V}$ $I_C = -100\text{mA}, V_{CE} = -1\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-0.25 -0.40	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.65 —	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.5	pF	$V_{CB} = -5.0\text{V}, f = 1\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	2.0	12	k Ω	$V_{CE} = -10\text{V}, I_C = -1\text{mA},$ $f = 1\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	10	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	3	60	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	$V_{CE} = -20\text{V}, I_C = -10\text{mA},$ $f = 100\text{MHz}$
Noise Figure	NF	—	4	dB	$V_{CE} = -5\text{V}, I_C = -100\mu\text{A},$ $R_S = 1\text{k}\Omega, f = 1\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	$V_{CC} = -3\text{V}, I_C = -10\text{mA},$ $V_{BE(off)} = -0.5\text{V}, I_{B1} = -1\text{mA}$
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	225	ns	$V_{CC} = -3\text{V}, I_C = -10\text{mA},$ $I_{B1} = -I_{B2} = -1\text{mA}$
Fall Time	t_f	—	75	ns	

 Note: 6. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics, PNP 3906 (@T_A = +25°C, unless otherwise specified.)

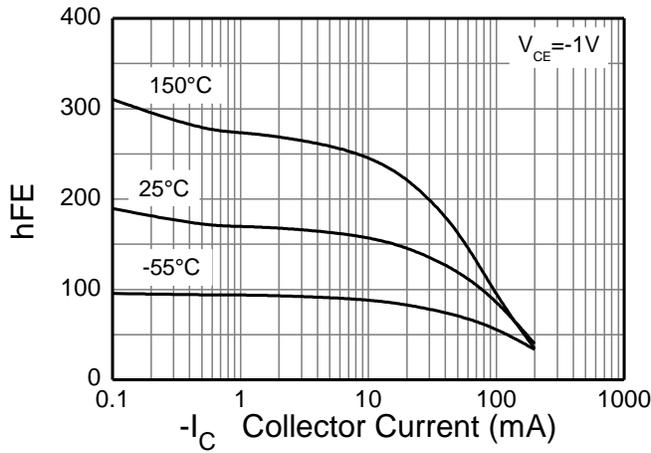


Fig. 12 $h_{FE} \ v \ I_C$

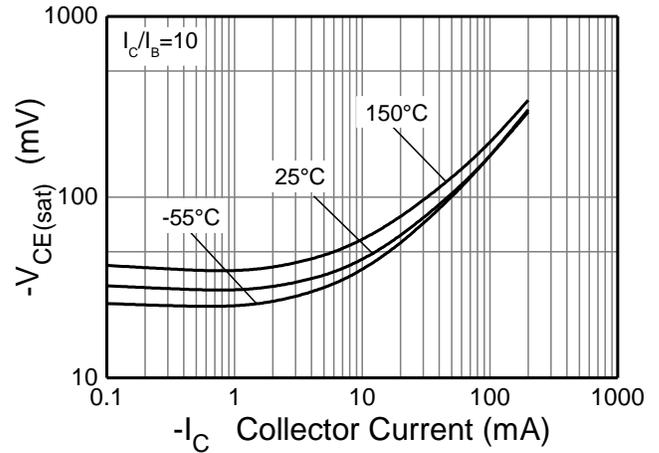


Fig. 13 $V_{CE(sat)} \ v \ I_C$

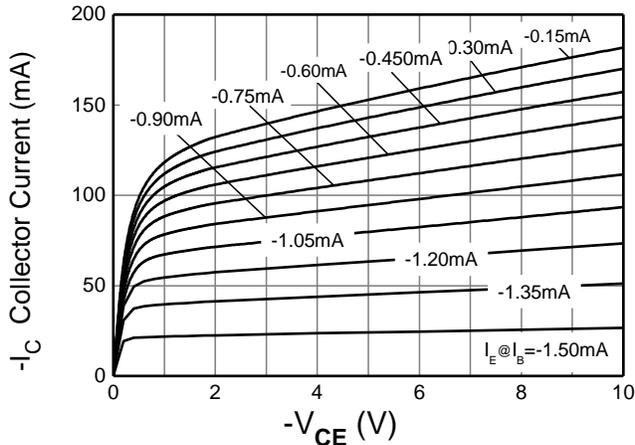


Fig. 14 $I_C \ v \ V_{CE}$

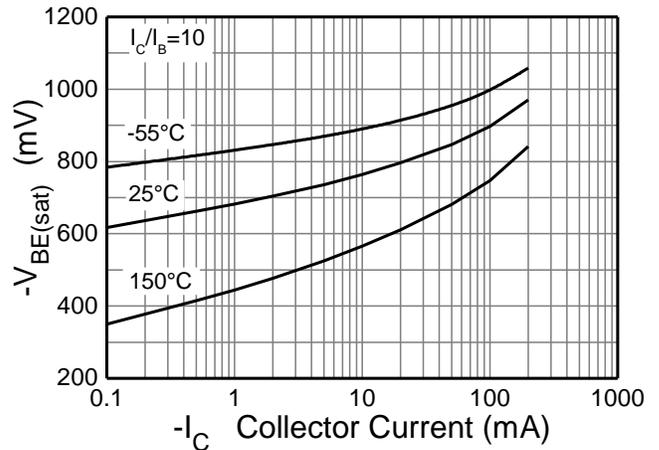


Fig. 15 $V_{BE(sat)} \ v \ I_C$

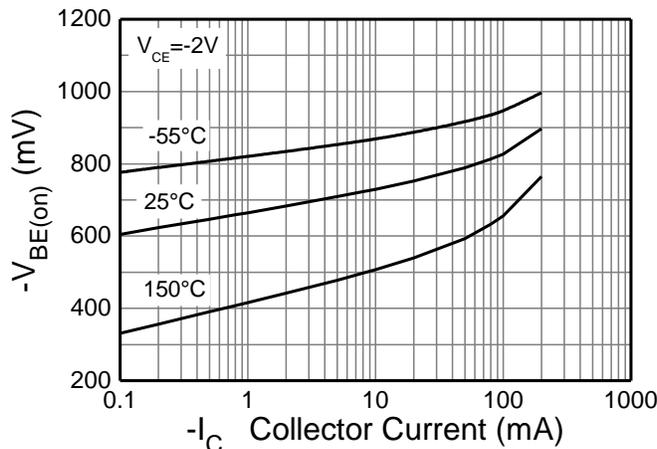


Fig. 16 $V_{BE(on)} \ v \ I_C$

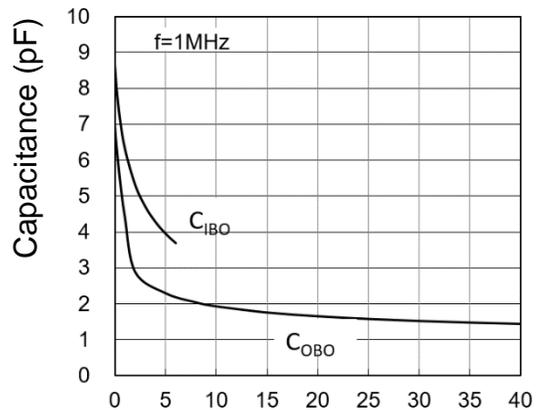
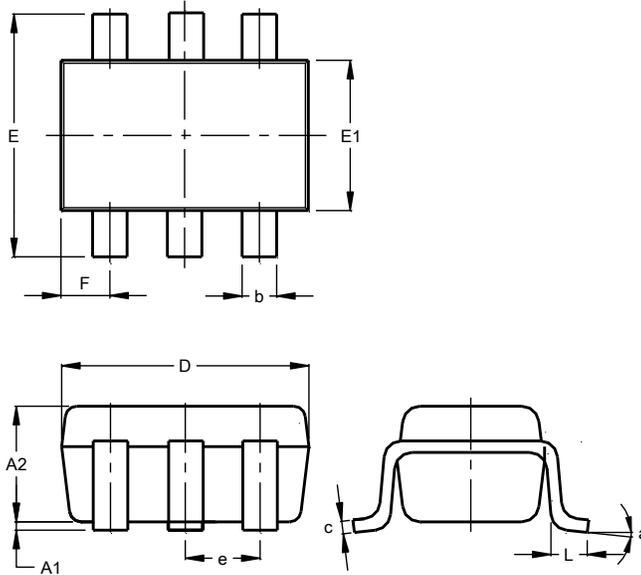


Fig. 17 Capacitance $v \ V_R$

Package Outline Dimensions

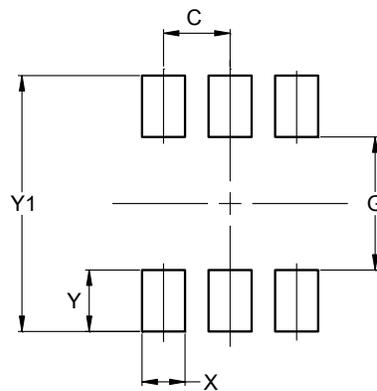
SOT363



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500